

## Descriptions

This 20A, 150V N-Channel MOSFET in a TO-252 Plastic Package.

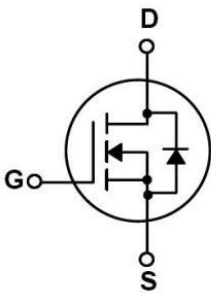
## Features

- Low  $R_{DS(on)}$
- Low gate charge
- Low  $C_{iss}$
- Fast switching
- Halogen-free Product

## Applications

Suited for low voltage applications such as automotive, DC/DC Converters, high efficiency switching for power management in portable and battery operated products, and power management interface card for TV or Monitor.

## Equivalent Circuit



## Pinning



PIN1: Gate    PIN 2: Drain    PIN 3: Source    PIN 4: Drain

## Absolute Maximum Ratings(Ta=25°C)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		$V_{DSS}$	150	V
Gate-Source Voltage		$V_{GS}$	±20	V
Continuous Drain Current	$T_C=25^\circ\text{C}$	$I_D$	20	A
	$T_C=100^\circ\text{C}$		13.5	
Pulsed Drain Current <sup>C</sup>		$I_{DM}$	35	
Avalanche Current <sup>C</sup>		$I_{AS}$	14.5	A
Avalanche energy L=0.1mH <sup>C</sup>		$E_{AS}$	12.5	mJ
Power Dissipation <sup>B</sup>	$T_C=25^\circ\text{C}$	$P_D$	105	W
	$T_C=100^\circ\text{C}$		41.5	
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55 to 150	°C
Maximum Junction-to-Ambient <sup>A</sup>	$t \leq 10\text{s}$	$R_{\theta JA}$	20	°C/W
Maximum Junction-to-Ambient <sup>AD</sup>	Steady-State		50	°C/W
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	1.4	°C/W

## Electrical Characteristics(Ta=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	150	156		V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=150\text{V}, V_{GS}=0\text{V}$ $T_J=125^\circ\text{C}$			1	$\mu\text{A}$
					5	
Gate-Body leakage current	$I_{GSS}$	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	2		4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}, I_D=10\text{A}$		59	90	mΩ
		$V_{GS}=7\text{V}, I_D=10\text{A}$		62	110	
Diode Forward Voltage	$V_{SD}$	$I_S=1\text{A}, V_{GS}=0\text{V}$			1	V

## Electrical Characteristics(Ta=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input Capacitance	$C_{iss}$	$V_{GS}=0V, V_{DS}=25V,$ $f=1MHz$		1700		pF
Output Capacitance	$C_{oss}$			4.5		
Reverse Transfer Capacitance	$C_{rss}$			58		
Gate resistance	$R_g$	$V_{GS}=0V, V_{DS}=0V$ $f=1MHz$		3.4		$\Omega$
Total Gate Charge	$Q_g(10V)$	$V_{GS}=10V, V_{DS}=75V,$ $I_D=10A$		15.5	22	nC
Total Gate Charge	$Q_g(4.5V)$			7	10	
Gate Source Charge	$Q_{gs}$			4		
Gate Drain Charge	$Q_{gd}$			1.2		
Turn-On Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=75V,$ $R_L=7.5\Omega, R_{GEN}=3\Omega$		6.5		ns
Turn-On Rise Time	$t_r$			5		
Turn-Off Delay Time	$t_{D(off)}$			23		
Turn-Off Fall Time	$t_f$			2.5		
Body Diode Reverse Recovery Time	$t_{rr}$	IF=10A, dI/dt=500A/ms		37		ns
Body Diode Reverse Recovery Charge	$Q_{rr}$	IF=10A, dI/dt=500A/ms		265		nC

- A. The value of  $R_{\theta JA}$  is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ C$ . The Power dissipation PDSM is based on  $R_{\theta JA}$  and the maximum allowed junction temperature of  $150^\circ C$ . The value in any given application depends on the user's specific board design, and the maximum temperature of  $150^\circ C$  may be used if the PCB allows it.
- B. The power dissipation  $P_D$  is based on  $T_{J(MAX)}=150^\circ C$ , using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
- C. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}=150^\circ C$ . Ratings are based on low frequency and duty cycles to keep initial  $T_J = 25^\circ C$ .
- D. The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to case  $R_{\theta JC}$  and case to ambient.

Electrical Characteristic Curve

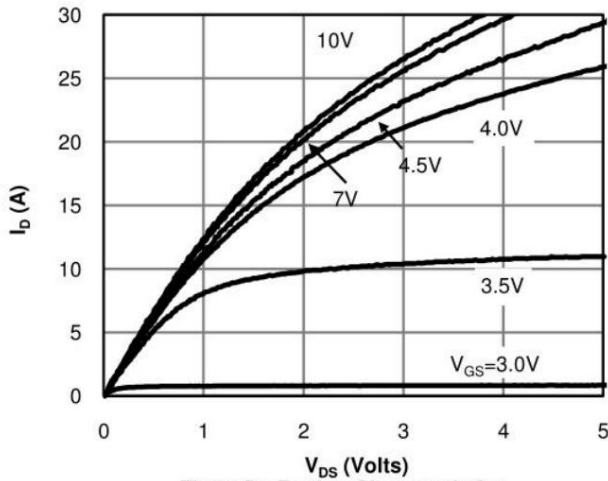


Fig 1: On-Region Characteristics

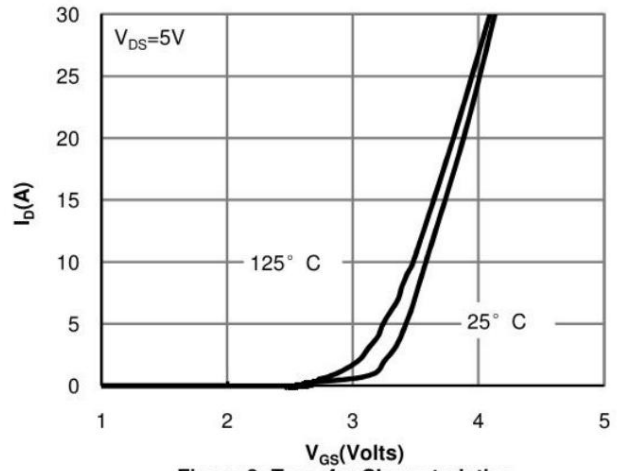


Figure 2: Transfer Characteristics

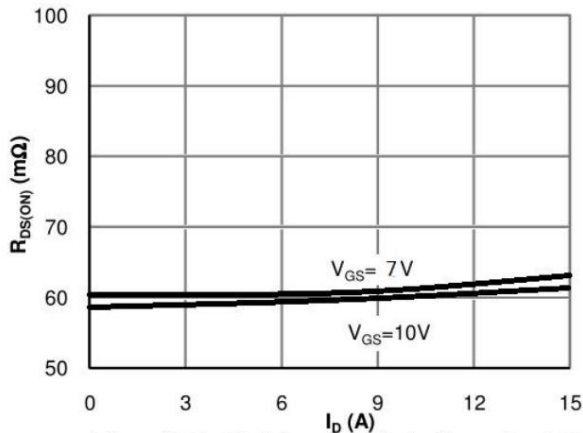


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

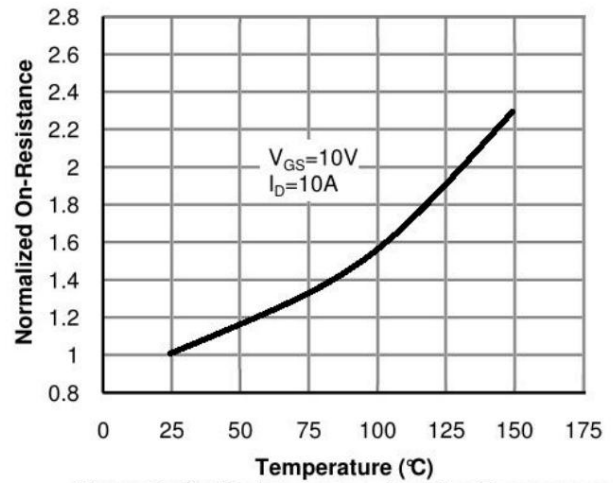


Figure 4: On-Resistance vs. Junction Temperature

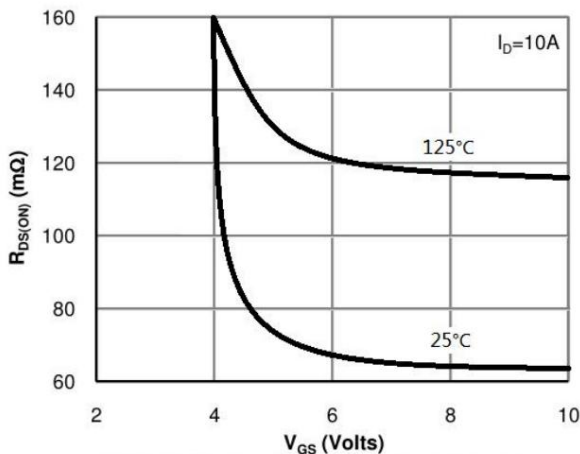


Figure 5: On-Resistance vs. Gate-Source Voltage

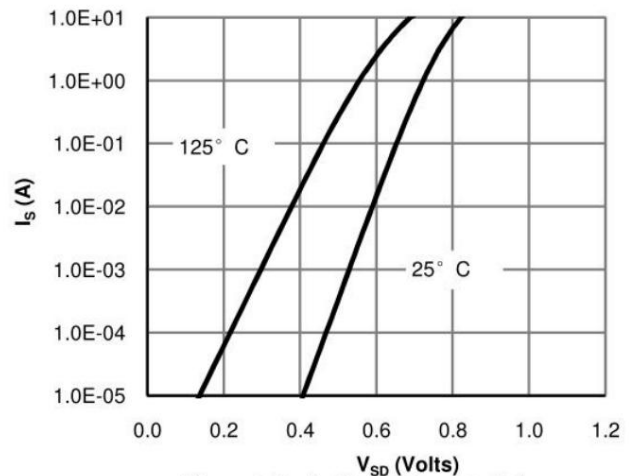


Figure 6: Body-Diode Characteristics

Electrical Characteristic Curve

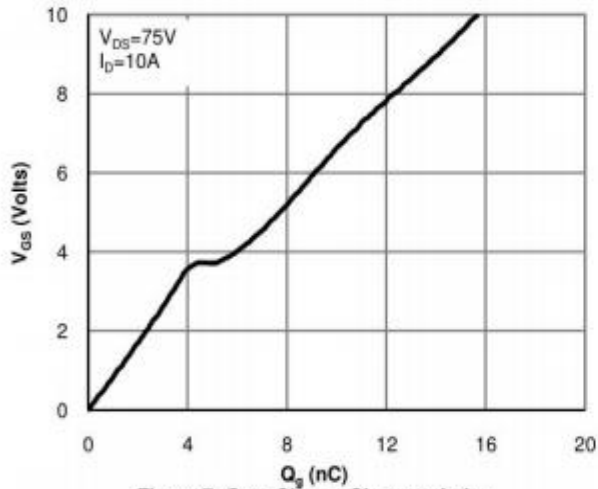


Figure 7: Gate-Charge Characteristics

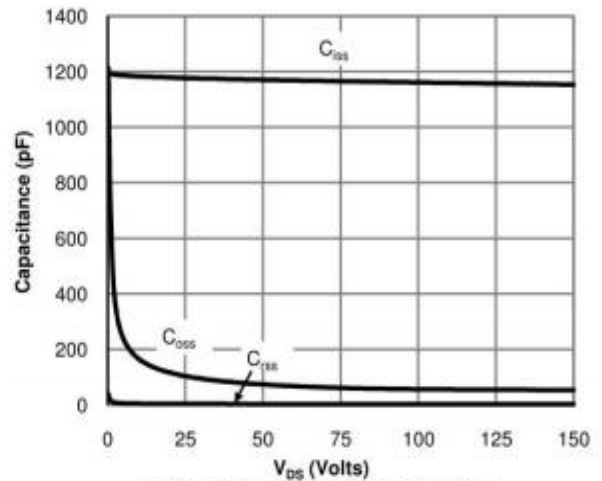


Figure 8: Capacitance Characteristics

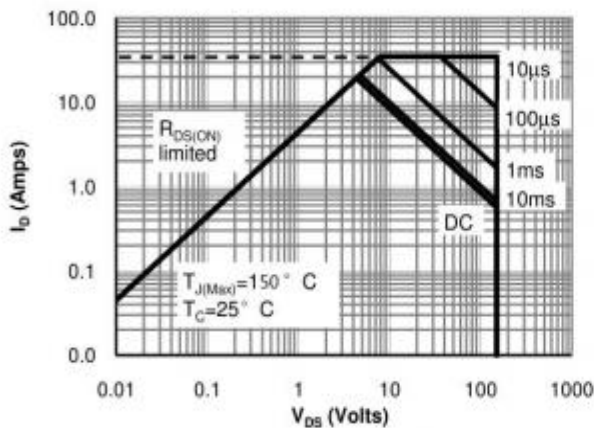


Figure 9: Maximum Forward Biased Safe Operating Area

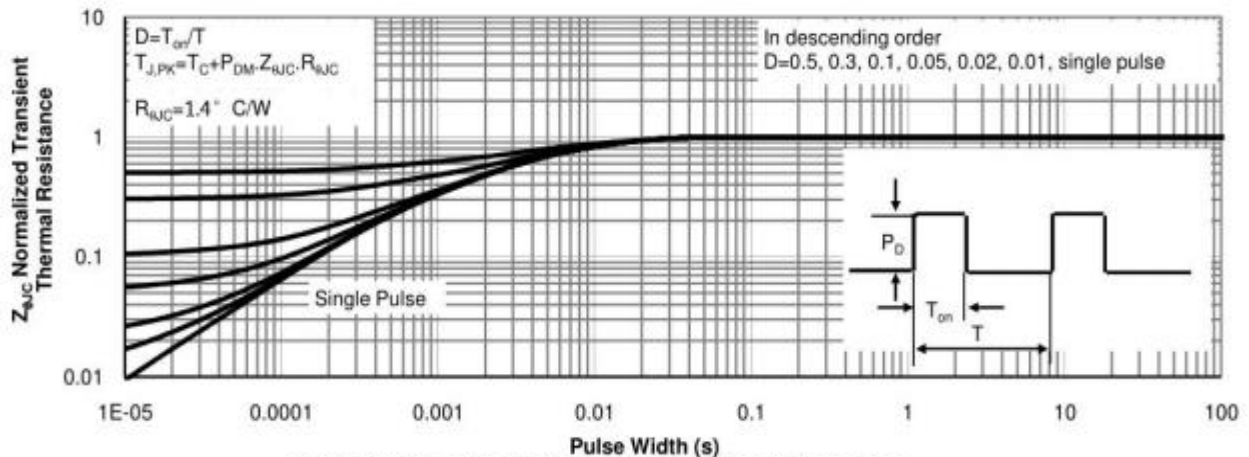
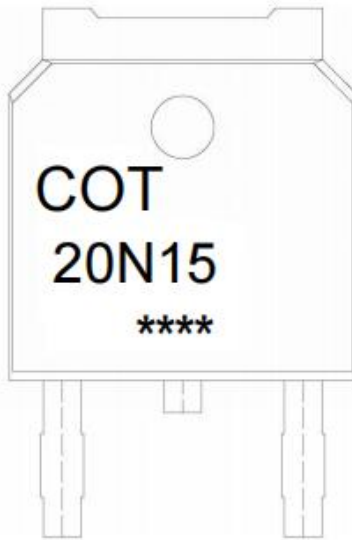


Figure 10: Normalized Maximum Transient Thermal Impedance

**Marking Instructions**



Note:

COT: Company Logo

20N15: Product Type.

\*\*\*\*: Lot No. Code, code change with Lot No.

**Packaging SPEC**

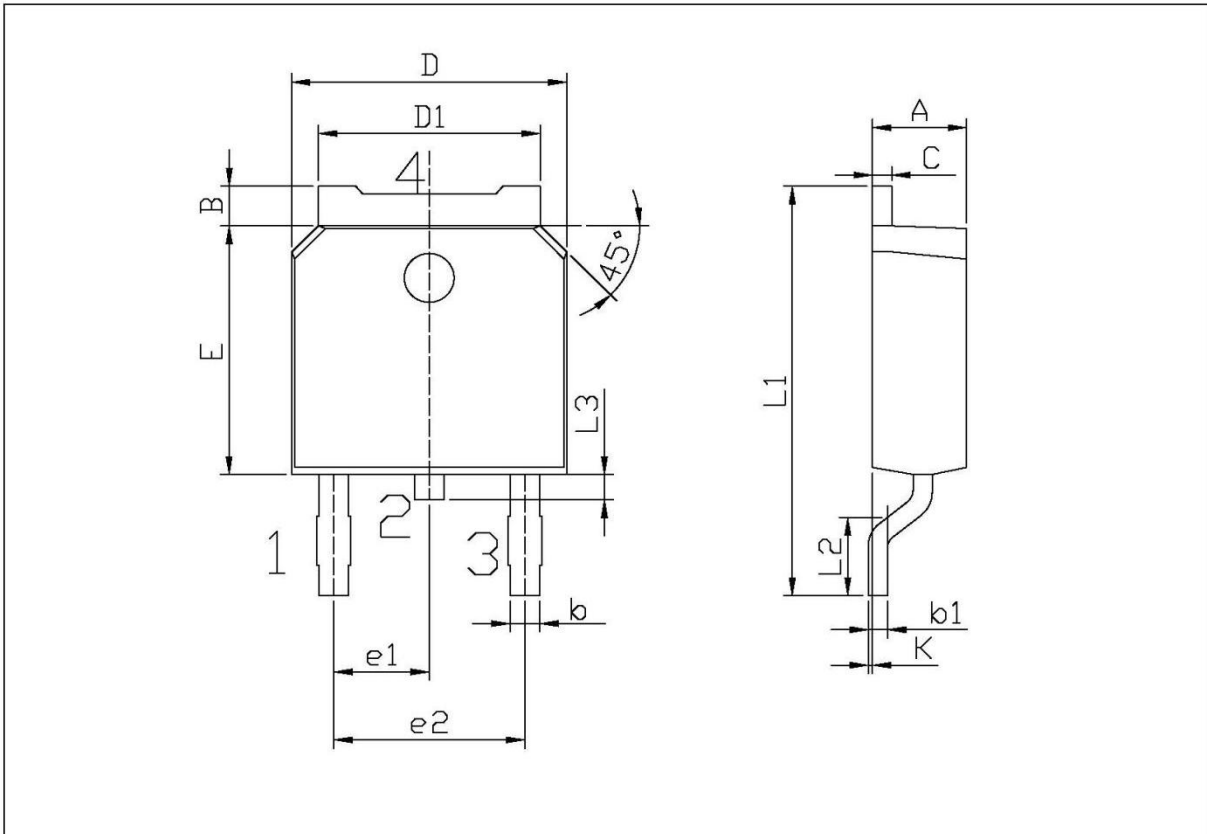
REEL INFORMATION

Package Type	Units					Dimension (unit: mm <sup>3</sup> )		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
TO-252	2,500	2	5,000	6	30,000	13" ×16	360×360×50	380×335×366

TUBE INFORMATION

Package Type	Units					Dimension (unit: mm <sup>3</sup> )		
	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Tube	Inner Box	Outer Box
TO-252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180

Package Outline Dimensions



单位: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	2.20	2.40	E	5.95	6.25
B	0.95	1.25	e1	2.24	2.34
b	0.70	0.90	e2	4.43	4.73
b1	0.45	0.55	L1	9.85	10.35
C	0.45	0.55	L2	1.70	2.00
D	6.45	6.75	L3	0.60	0.90
D1	5.10	5.50	K	0.00	0.10

TO-252